

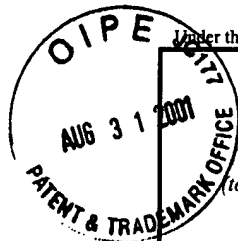
Please type a plus sign (+) inside this box → [ + ]

PTO/SB/21 (08-00)

Approved for use through 10/31/2002. OMB 0657-0021

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.



<b>TRANSMITTAL FORM</b> (to be used for all correspondence after initial filing)	Application Number	09/695,414
	Filing Date	October 25, 2000
	First Named Inventor	Hongyong ZHANG et al.
	Group Art Unit	2813
	Examiner Name	E. Pert
Total Number of Pages in This Submission	Attorney Docket Number	740756-2218

**ENCLOSURES (check all that apply)**

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Other
Remarks		<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 19-2380 for the above identified docket number.

**SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT**

Firm or Individual name	<u>Eric J. Robinson, Reg. No. 38,285</u> Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22012
Signature	
Date	August 31, 2001

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on this date: <span style="border: 1px solid black; display: inline-block; width: 100px; height: 20px; vertical-align: middle;"></span>			
Type or printed name			
Signature		Date	

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.



- 1 -

Docket No. 740756-2218

9/6/01  
Harrison

RECEIVED

SEP -4 2001

In re Patent Application of )  
Hongyong ZHANG et al. )  
Serial No. 09/695,414 ) Group Art Unit: 2813  
Filed: October 25, 2000 ) Examiner: E. Pert  
For: METHOD FOR FORMING )  
SEMICONDUCTOR DEVICE )

TECHNOLOGY CENTER 2800

AMENDMENT

Honorable Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action mailed May 31, 2001, please amend the above identified application as follows.

IN THE CLAIMS:

Please amend claims 1, 4, 7, 10, 13 and 16 as follows. A marked-up version of the amended claims is attached.

1. (Amended) A method of manufacturing a semiconductor device comprising the steps of:
- forming a semiconductor film comprising amorphous silicon on an insulating surface;
  - forming a crystallization promoting material comprising a metal in contact with said semiconductor film in a chamber; and
  - crystallizing said semiconductor film in contact with said crystallization promoting material in said chamber,
- wherein the step of crystallizing said semiconductor film is carried out successively after the formation of said crystallization promoting material without exposing said semiconductor film and said crystallization promoting material to the air outside said chamber.